SCHOTTKY BARRIER DIODE

LRB751S–40T1G

Features

(1)Small surface mounting type SC-79/SOD523

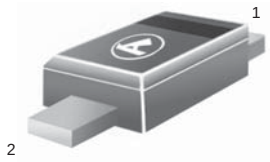
(2)Low reverse current and low forward voltage.

(3)High reliability

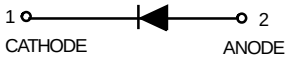
Construction

silicon epitaxial planar

We declare that the material of product compliance with RoHS requirements.



SOD - 523



MAXIMUM RATINGS (T_A = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	30	V
Mean rectifying current	I_O	30	mA
Peak forward surge current	I_{FSM}	200	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C

DEVICE MARKING

LRB751S–40T1G= 5

ELECTRICAL CHARACTERISTICS(T_A = 25°C)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Forward voltage	V_F	–	–	0.37	V	I_F=1mA
Reverse current	I_R	–	–	0.5	μA	V_R=30V
Capacitance between terminals	C_T	–	2.0	–	pF	V_R=1V,f=1MHz

Ordering Information

Device	Marking	Shipping
LRB751S-40T1G	5	3000/Tape&Reel
LRB751S-40T3G	5	10000/Tape&Reel

LRB751S–40T1G

Electrical characteristic curves(T_A = 25°C)

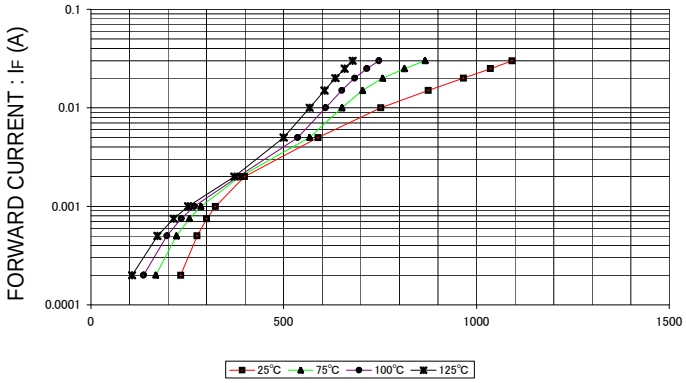


Fig. 1 Forward characteristics

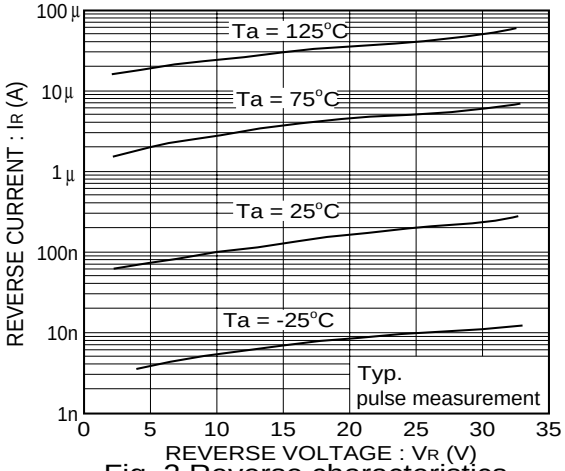


Fig. 2 Reverse characteristics

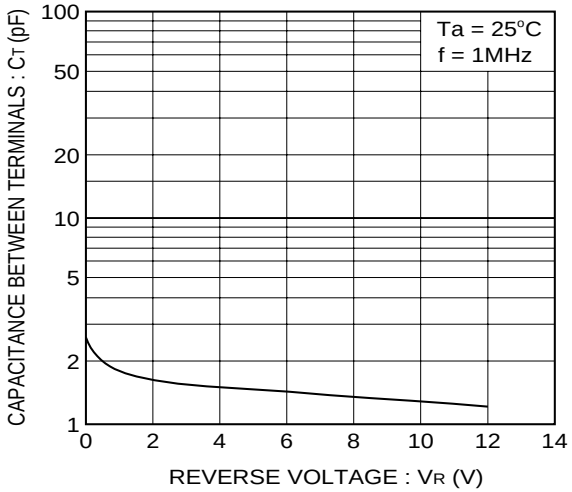
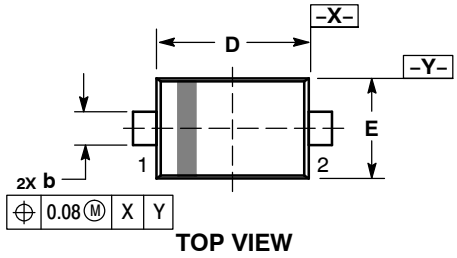


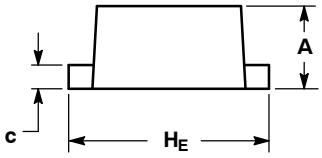
Fig. 3 Capacitance between terminals characteristics

LRB751S–40T1G

SC–79/SOD–523



TOP VIEW

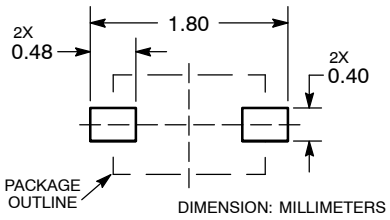


SIDE VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.50	0.60	0.70
b	0.25	0.30	0.35
c	0.07	0.14	0.20
D	1.10	1.20	1.30
E	0.70	0.80	0.90
H_E	1.50	1.60	1.70
L	0.30 REF		
L_2	0.15	0.20	0.25

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSION: MILLIMETERS